

## Speaker Profile

	<p><b>Name : Heon-Min Lee</b></p> <p><b>Title : Chief Research Engineer</b></p> <p><b>Institute : LG Electronics Institute of Technology Devices &amp; Materials Lab.</b></p> <p>1986.3 ~ 1992.2 Physics, SKKU, B.S. 1992.3 ~ 1994.2 Physics, POSTECH, M.S. 1999.3 ~ 2005.8 Electrical &amp; Electronic Engineering, KAIST, Ph. D.</p> <p>1994.1~ 1996.2 Research engineer at LG Elite 1996.3~ 1999.2 Junior Research engineer at LG Elite 1999.3 ~ 2002.2 Senior Research engineer at LG Elite 2003.3 ~ Present Chief Research engineer at LG Elite</p> <p>1994.1~ 1995.2 Development of motion detector using pyroelectric (Pb, La)TiO<sub>3</sub> thin films grown on MgO and on Pt/MgO</p> <p>1996.3~ 1997.2 Development of high dielectric Ba<sub>1-x</sub>Sr<sub>x</sub>TiO<sub>3</sub> thin films as a capacitor dielectric material for GBit DRAMs</p> <p>1997.3~ 2000.2 Development of nonvolatile ferroelectric memory using a novel dry etching technology</p> <p>2000.3~ 2003.2 Development of Thin Film Bulk Acoustic Resonators (TFBARs) for advanced handset applications</p> <p>2003.3~ 2005.9 Development of miniaturized SnO<sub>2</sub> chemical sensor modules for advanced handset applications</p> <p>2005.10~ Present Development of Si thin film based solar cell</p>
<p><b>Contact Details</b></p> <p><b>Organization Name:</b> LG Electronics Institute of Technology Devices &amp; Materials Lab. SE Group</p> <p><b>Address:</b> 16 Woomyeon-Dong, Seocho-Gu, Seoul 137-724, Korea</p> <p><b>Phone:</b> +82-2-526-4486 +82-19-9495-0815</p> <p><b>Email:</b> hmlee@lge.com</p>	